

FIG. 1

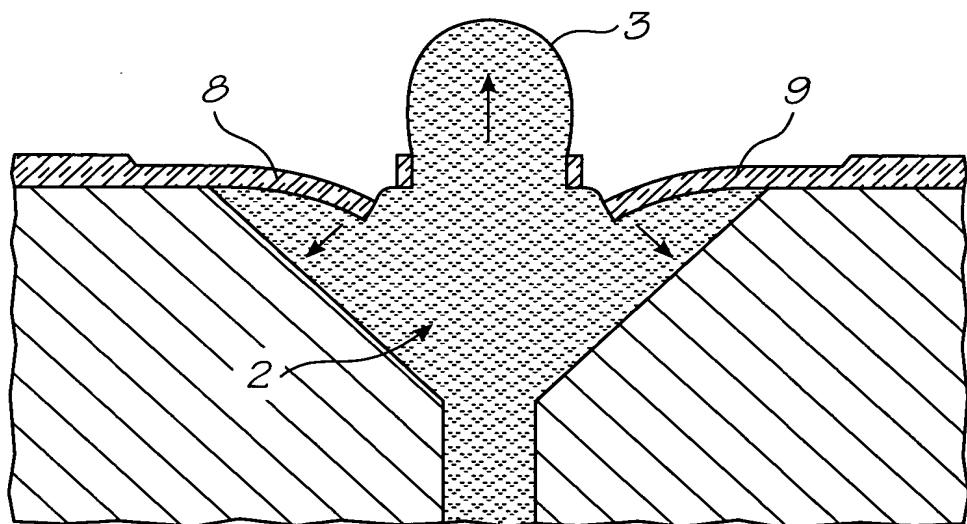


FIG. 2

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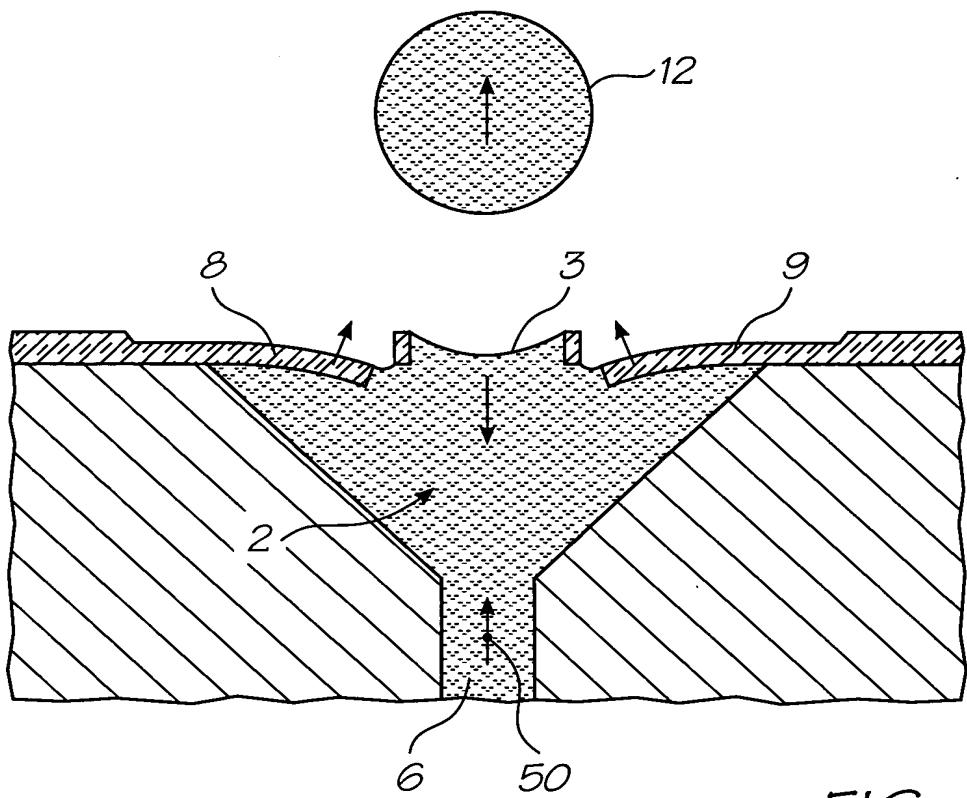


FIG. 3

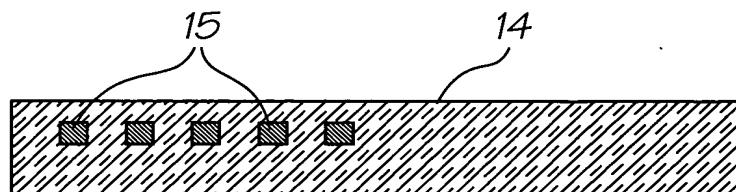


FIG. 4A

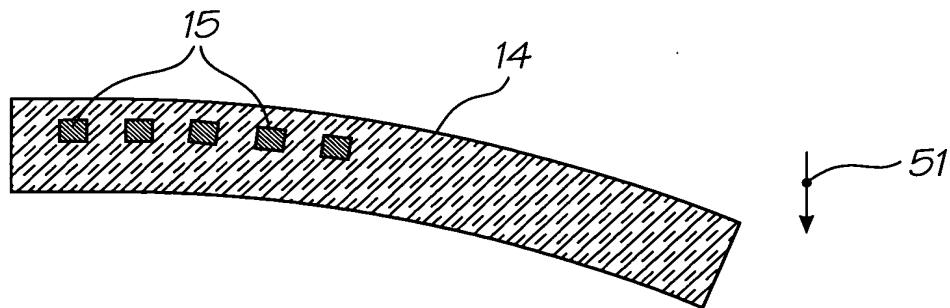


FIG. 4B

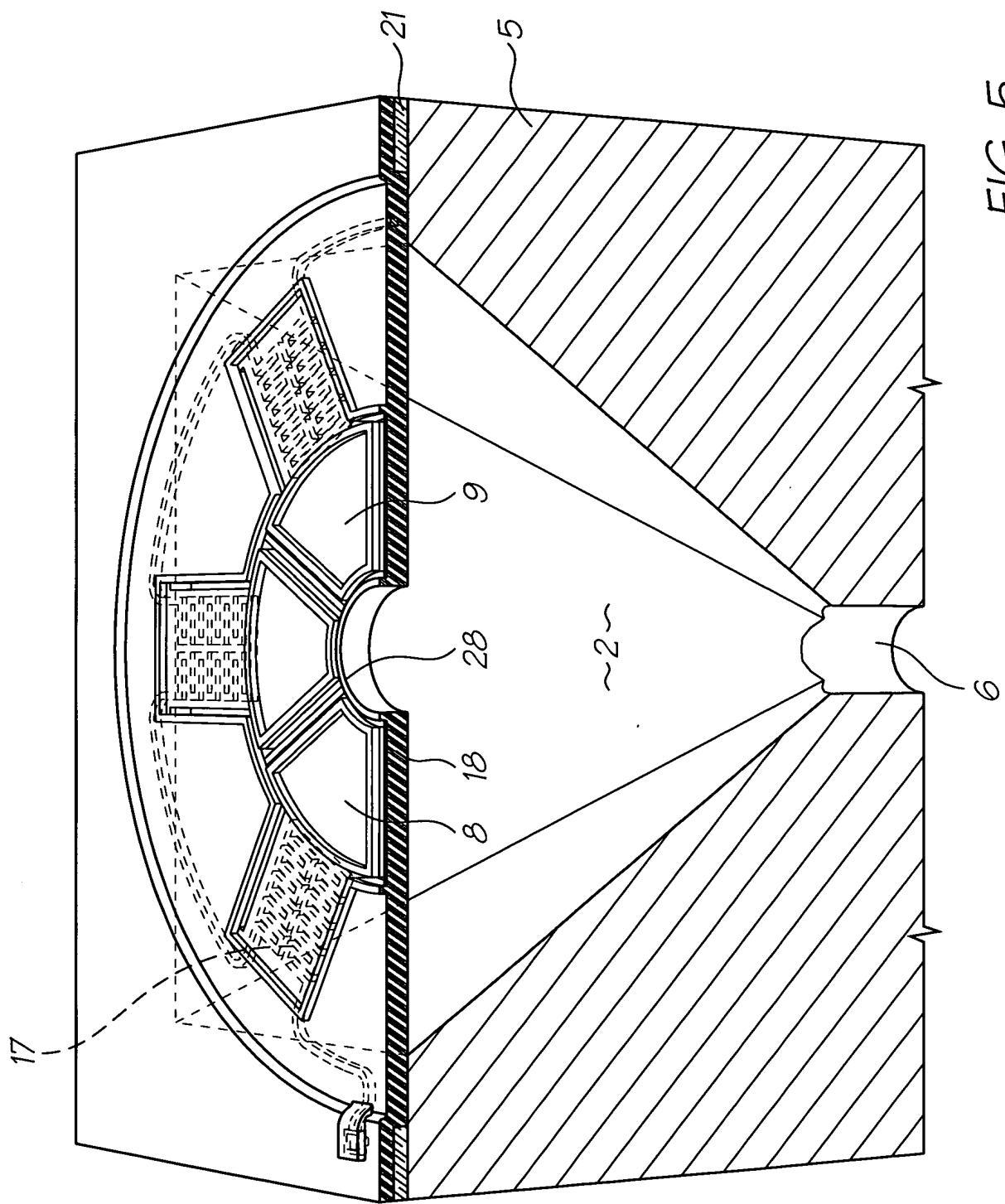


FIG. 5

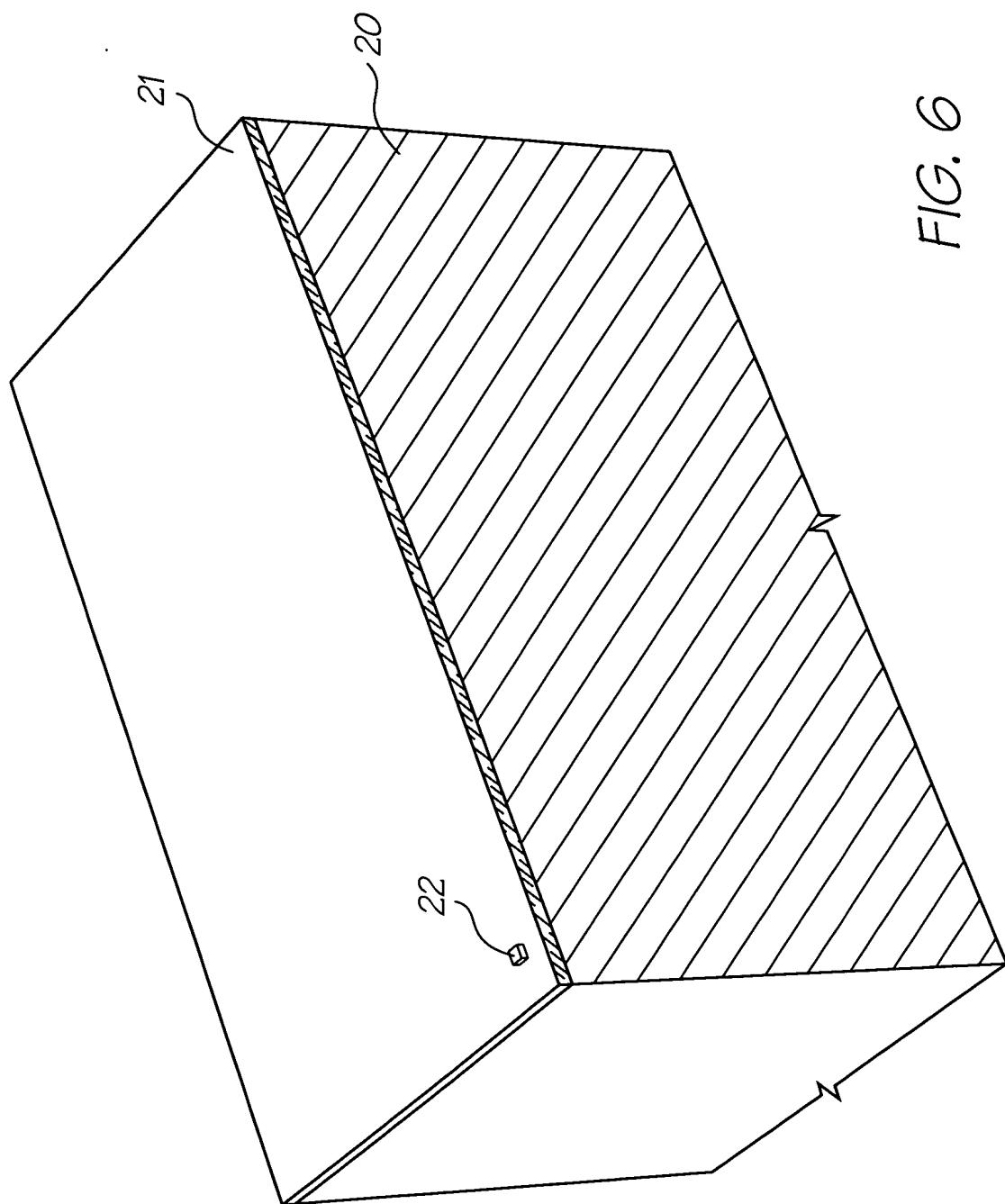


FIG. 6

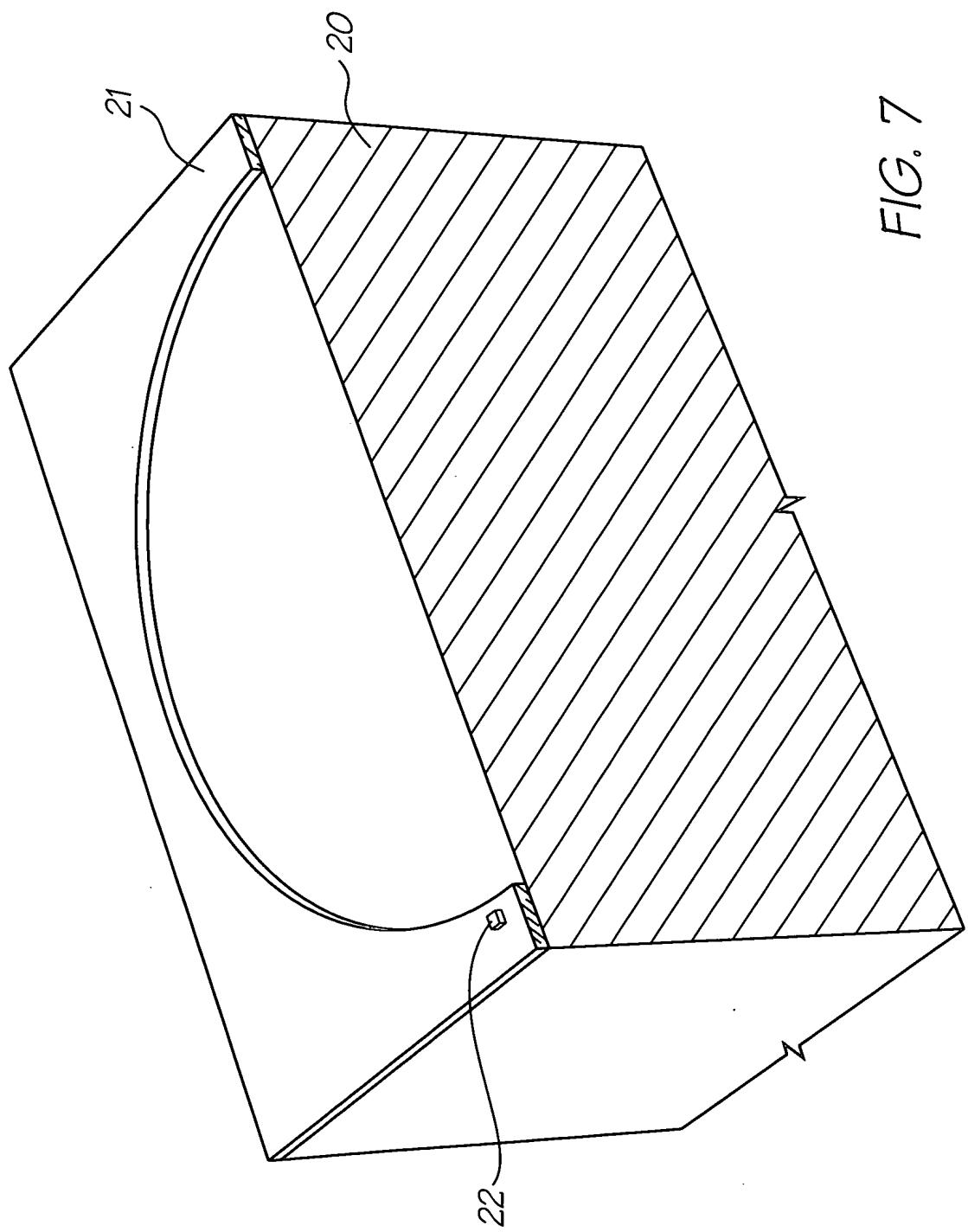


FIG. 7

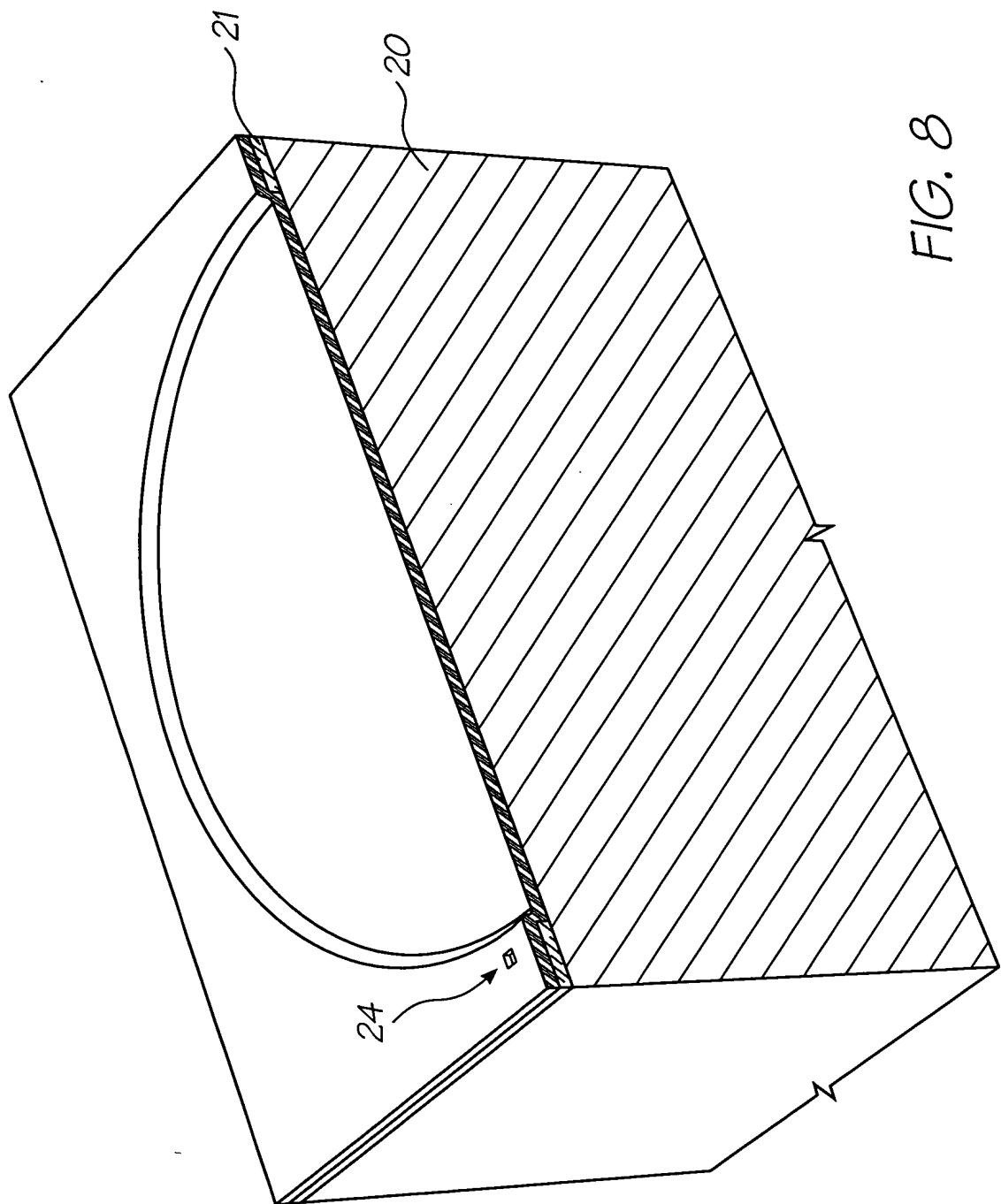


FIG. 8

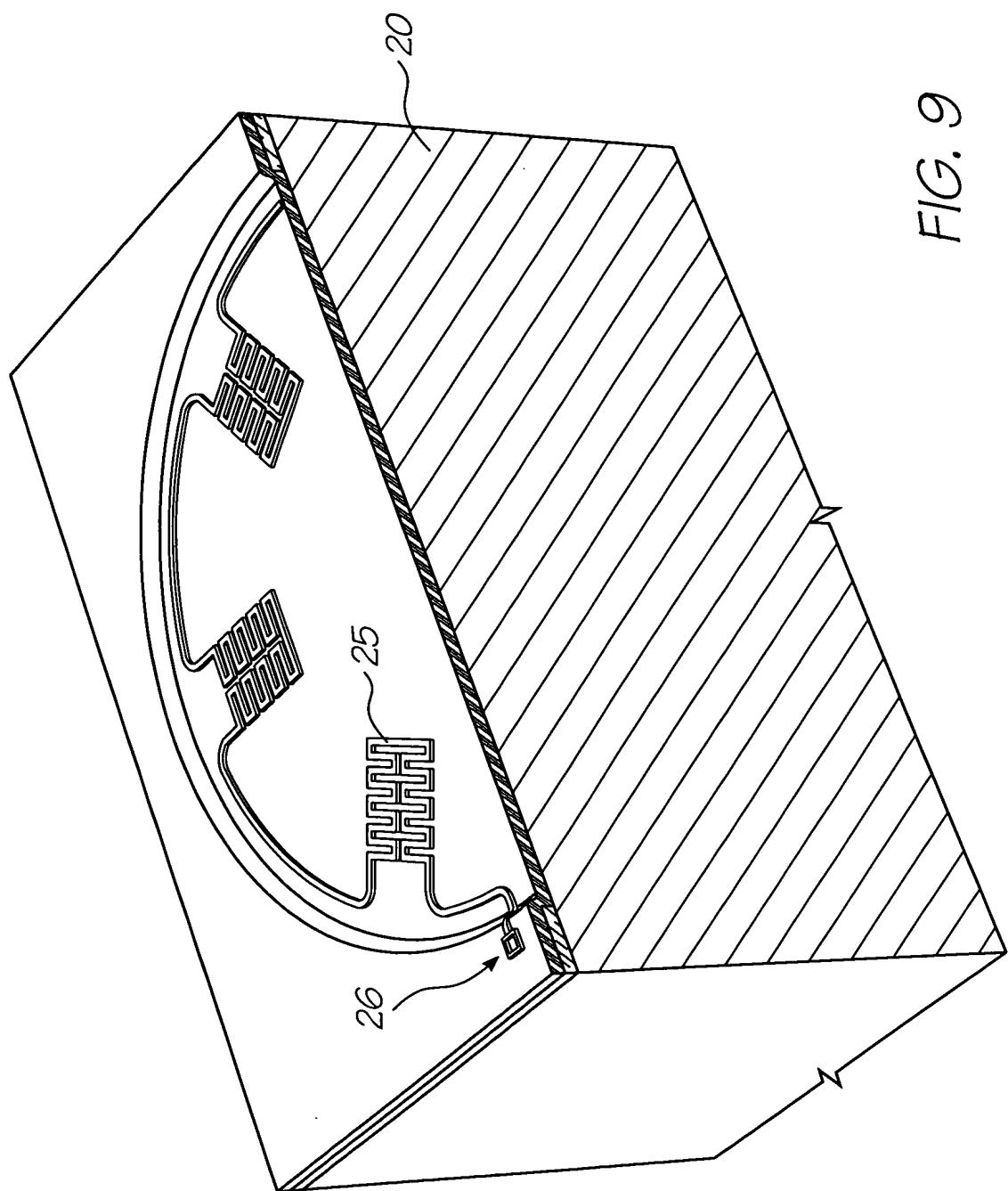
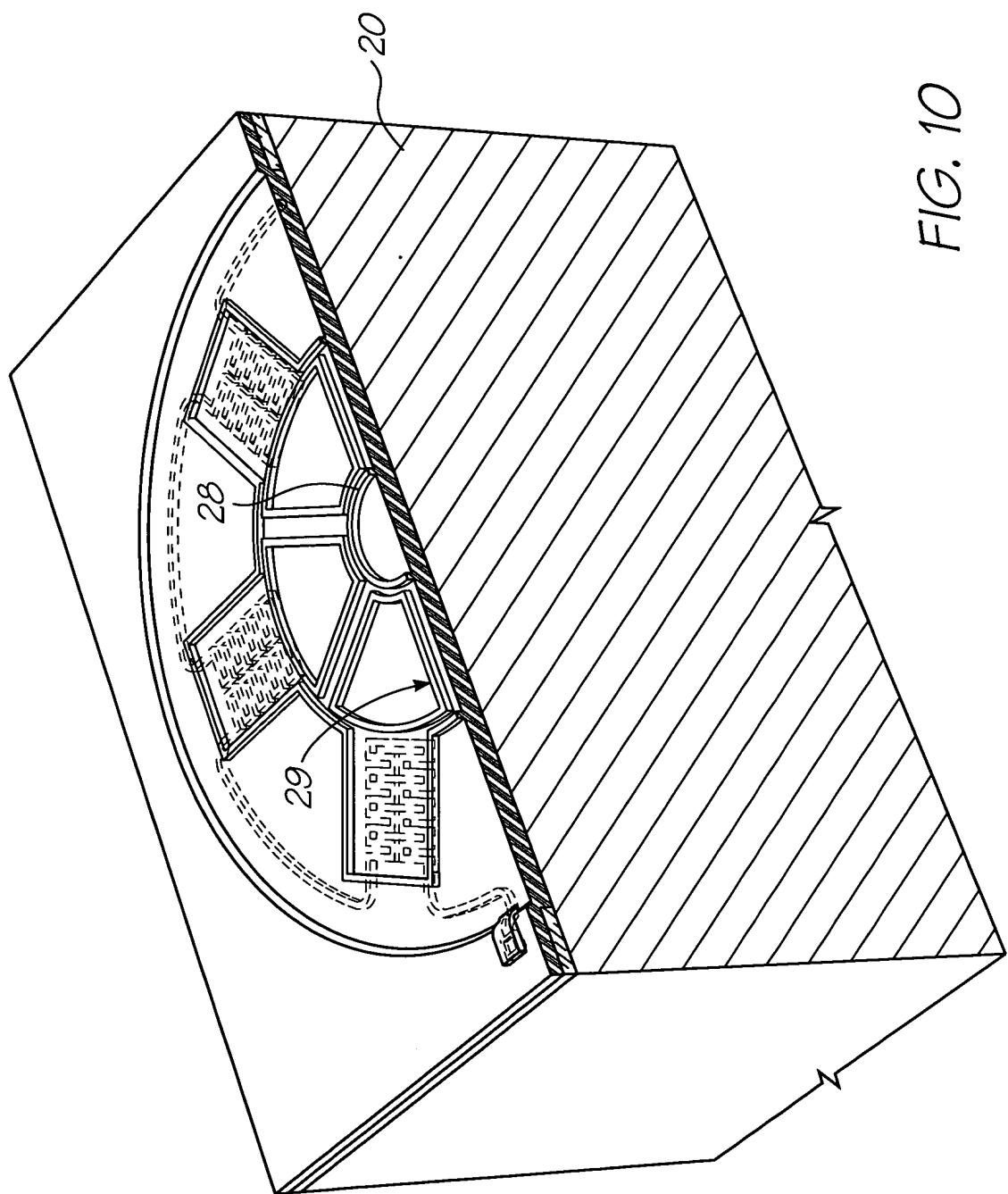


FIG. 9

FIG. 10



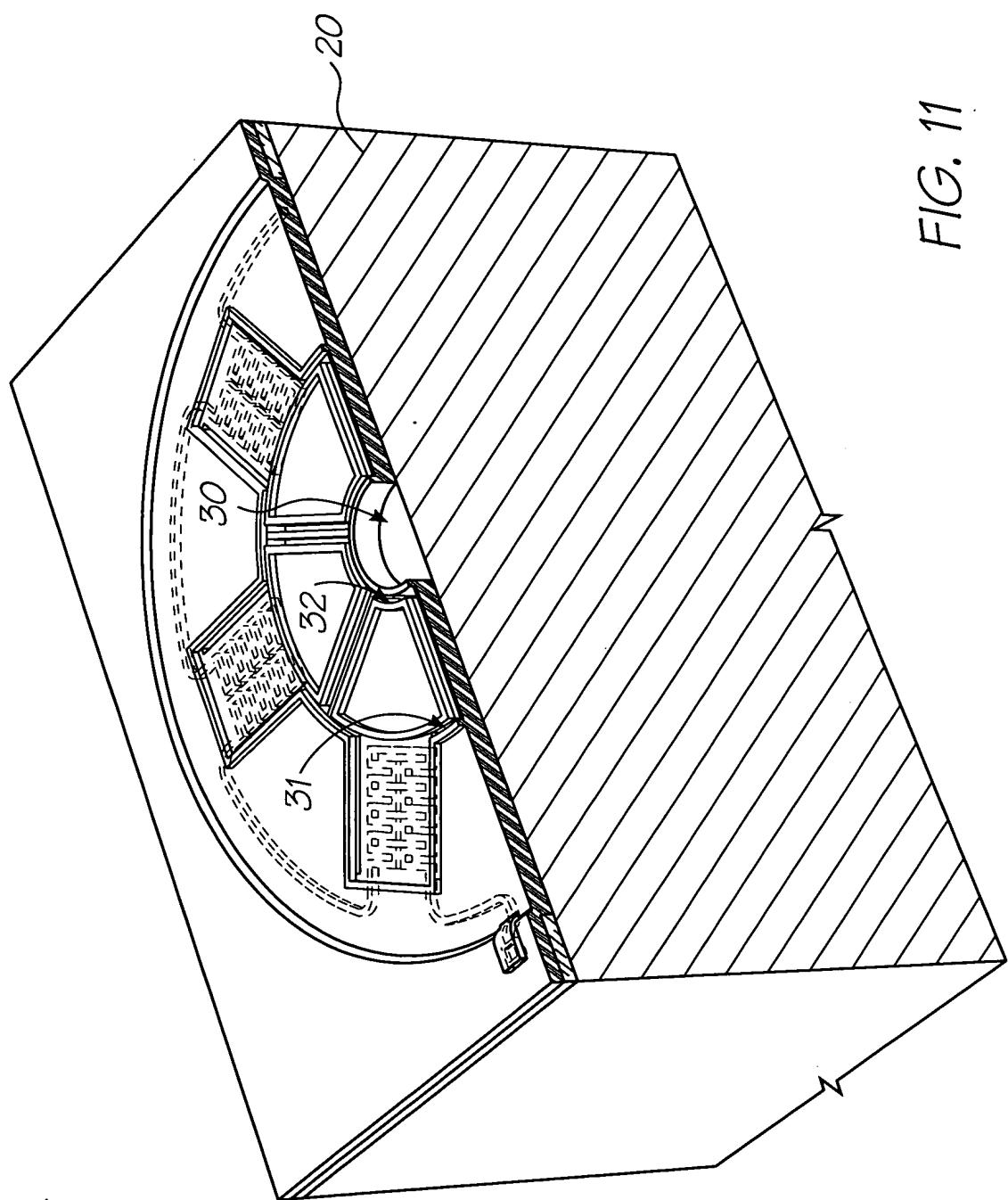


FIG. 11

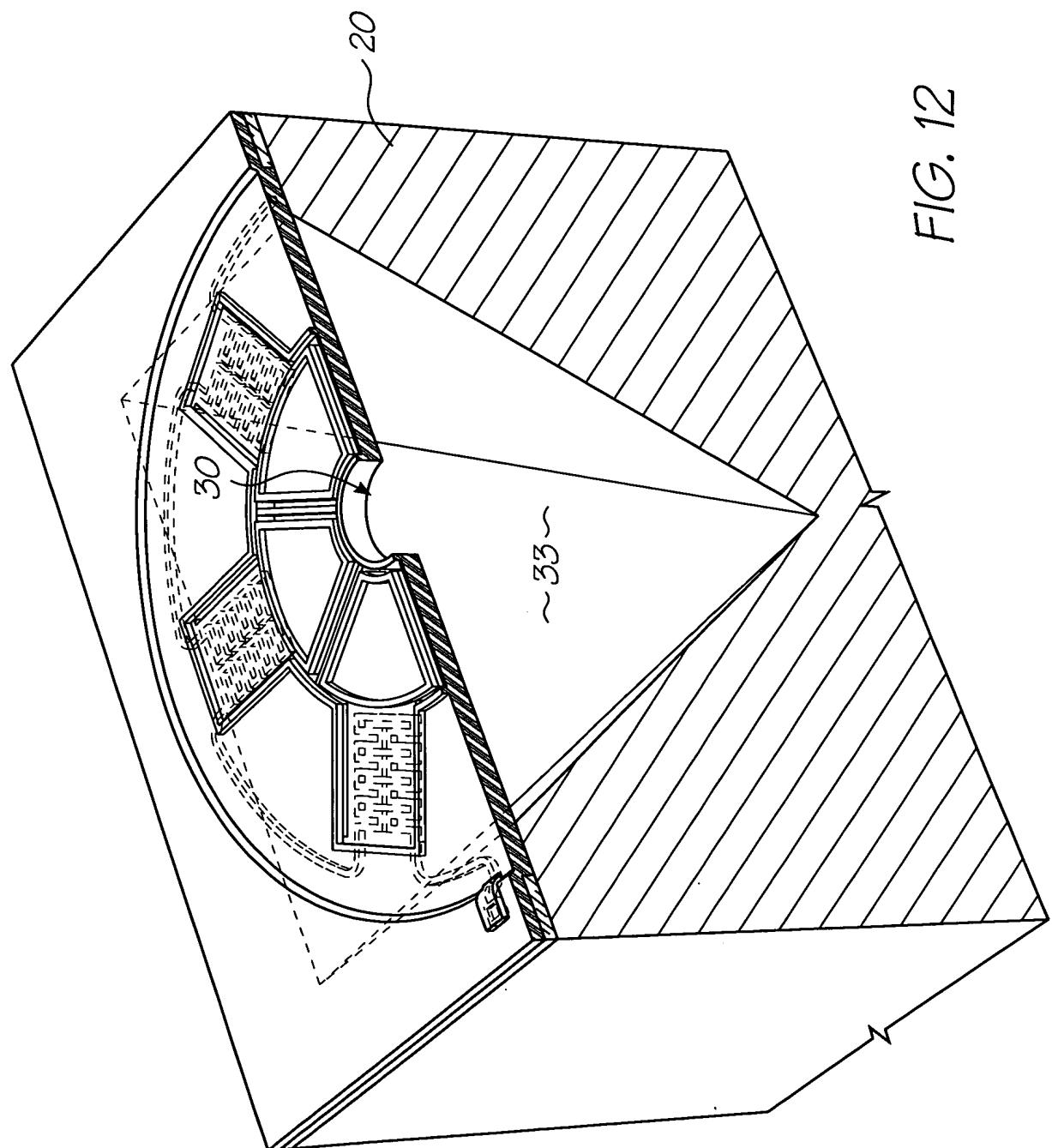
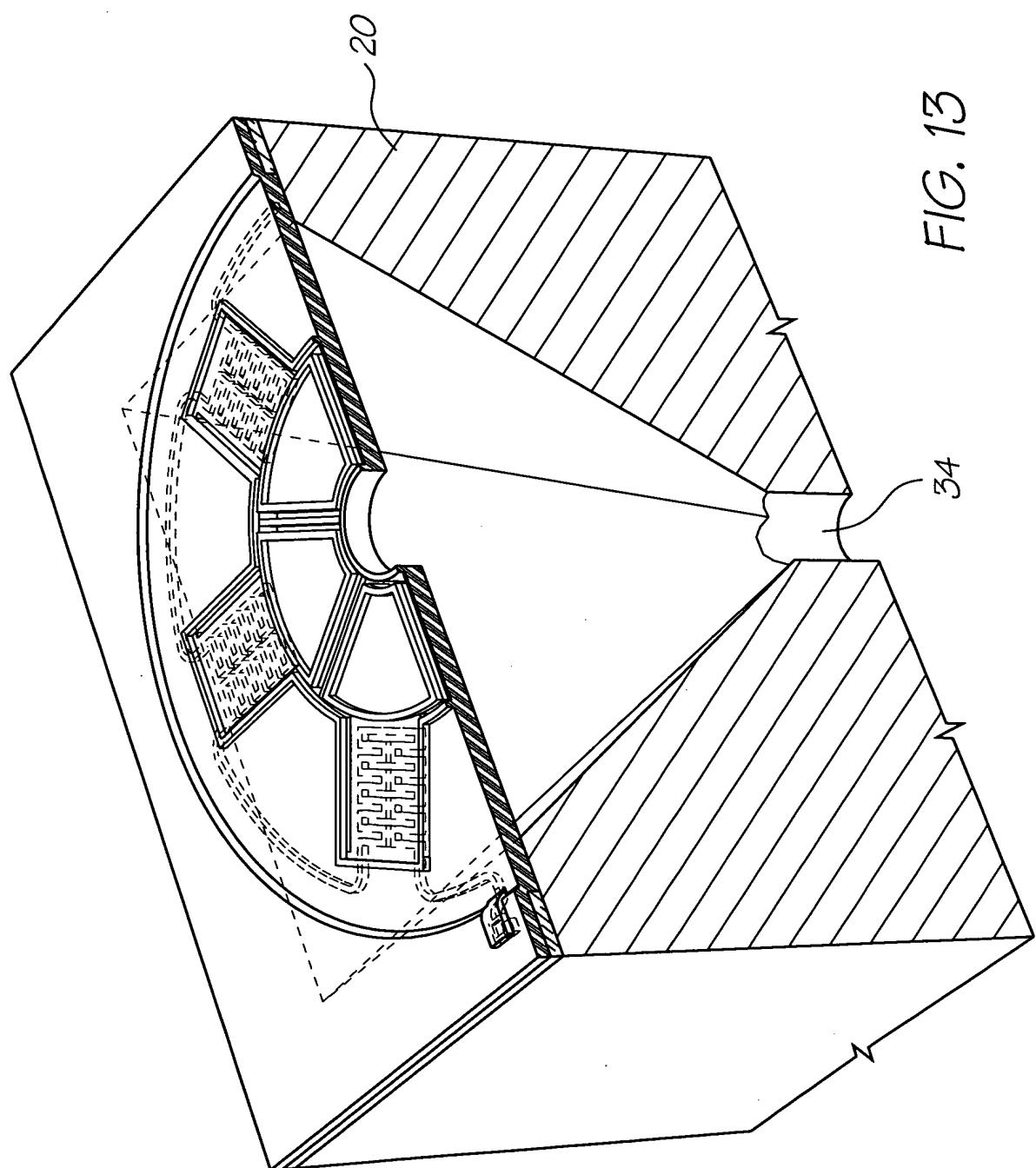


FIG. 12

FIG. 13



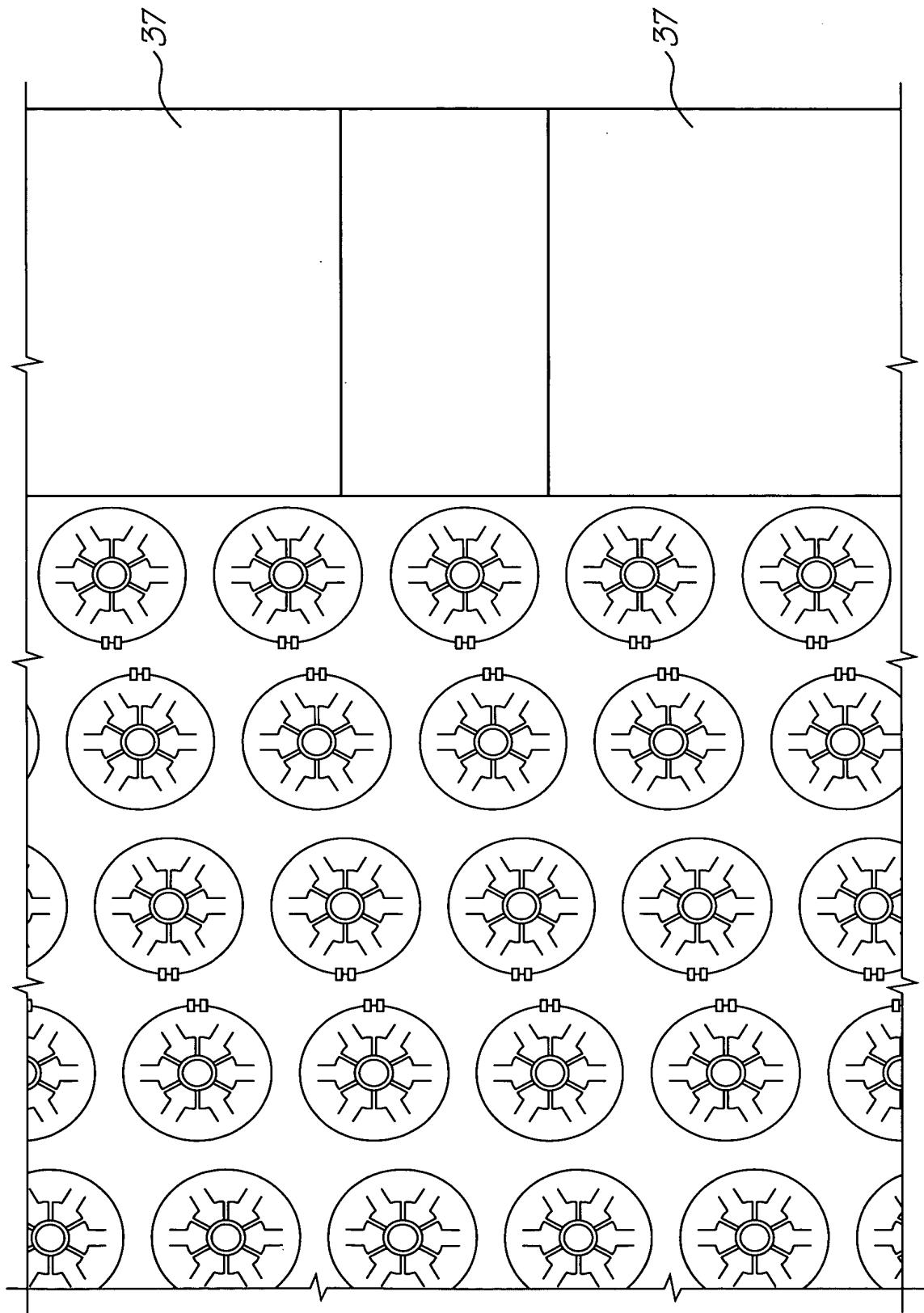


FIG. 14

	Silicon		Sacrificial material		Elastomer
	Boron doped silicon		Cupronickel		Polyimide
	Silicon nitride (Si_3N_4)		CoNiFe or NiFe		Indium tin oxide (ITO)
	CMOS device region		Permanent magnet		PTFE
	Aluminum		Polysilicon		Conductive PTFE
	Glass (SiO_2)		Titanium Nitride (TiN)		Terfenol-D
	Copper		Titanium boride (TiB_2)		Shape memory alloy
	Gold		Adhesive		Tantalum
			Resist		Ink

FIG. 15

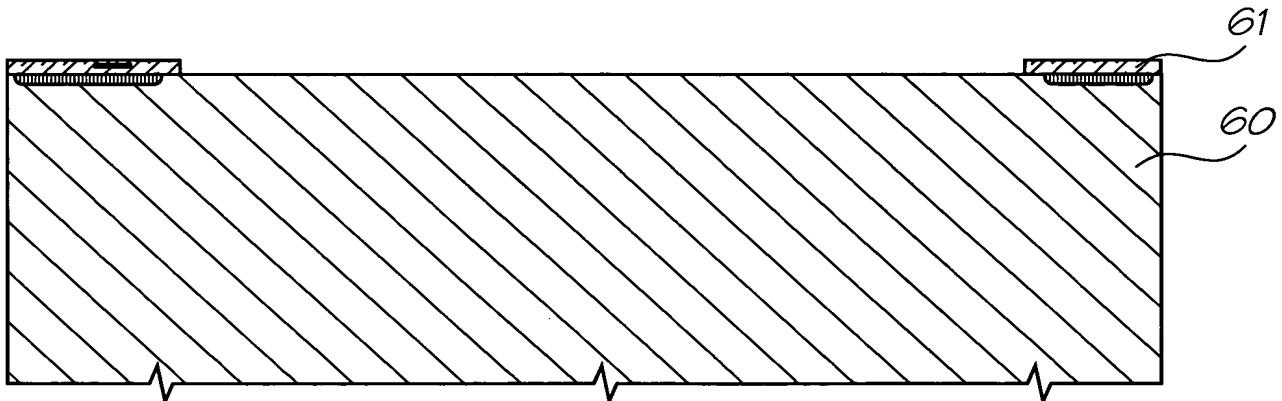


FIG. 16

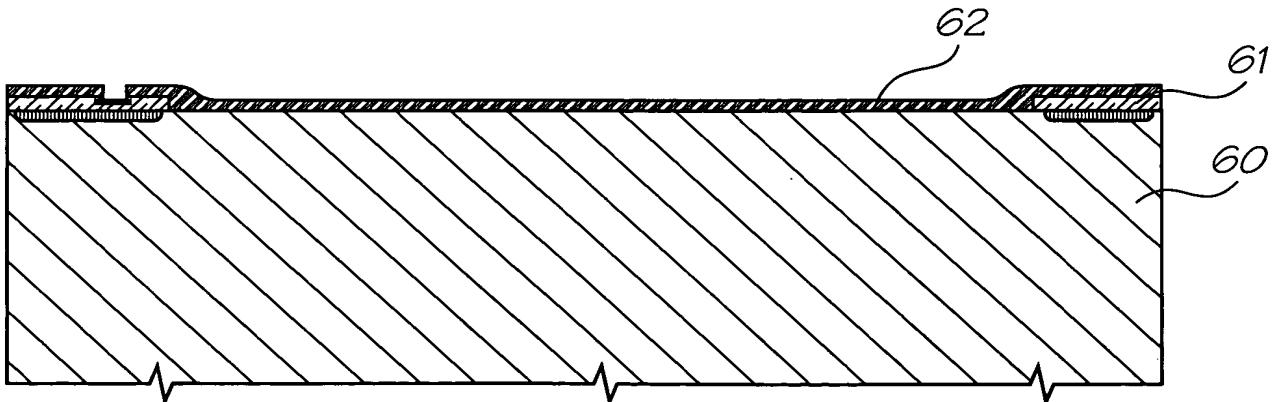


FIG. 17

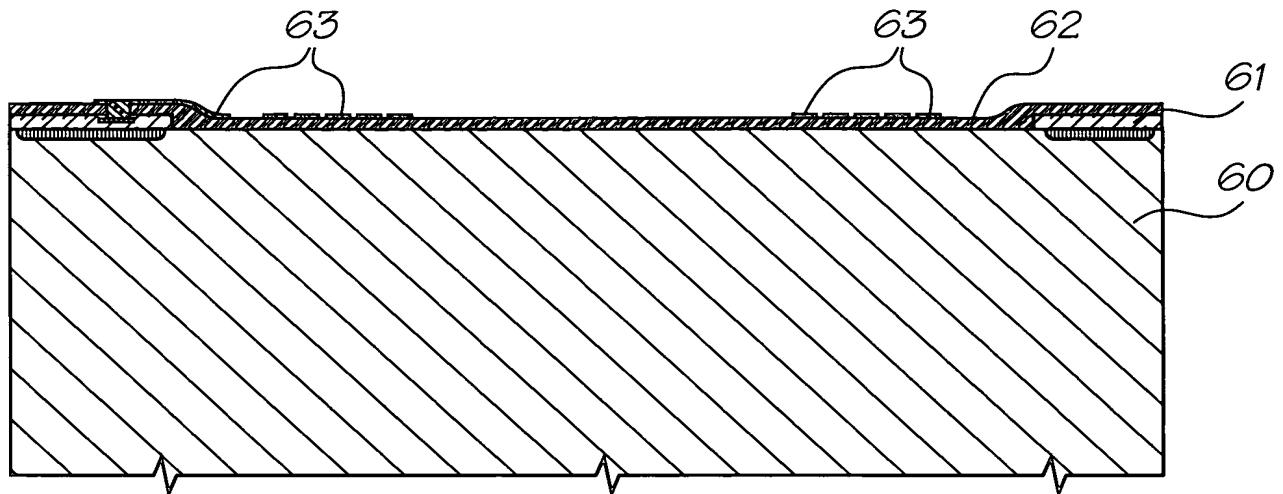


FIG. 18

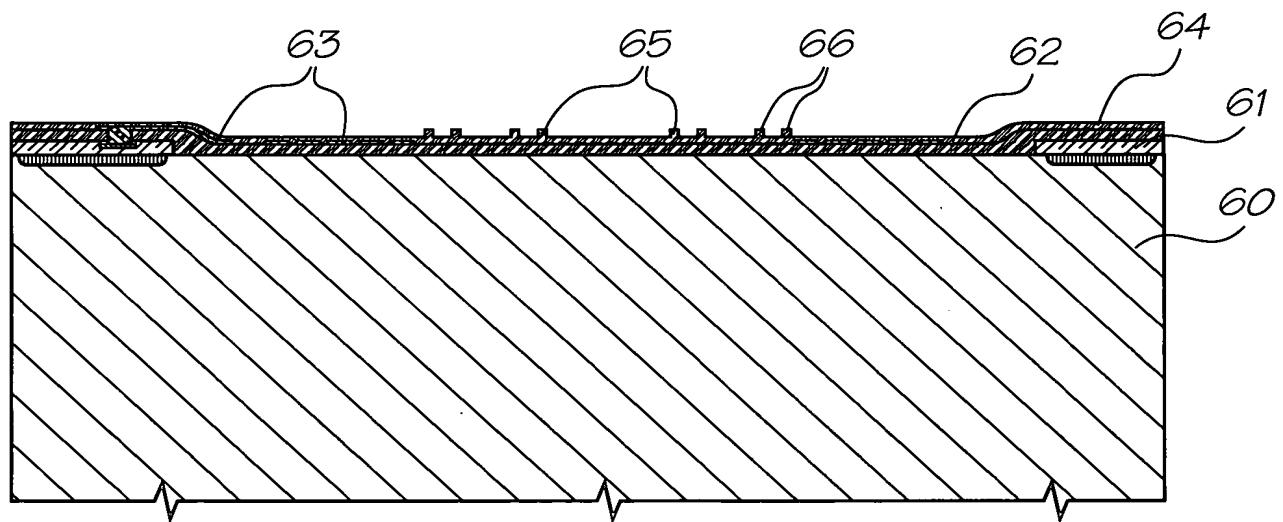


FIG. 19

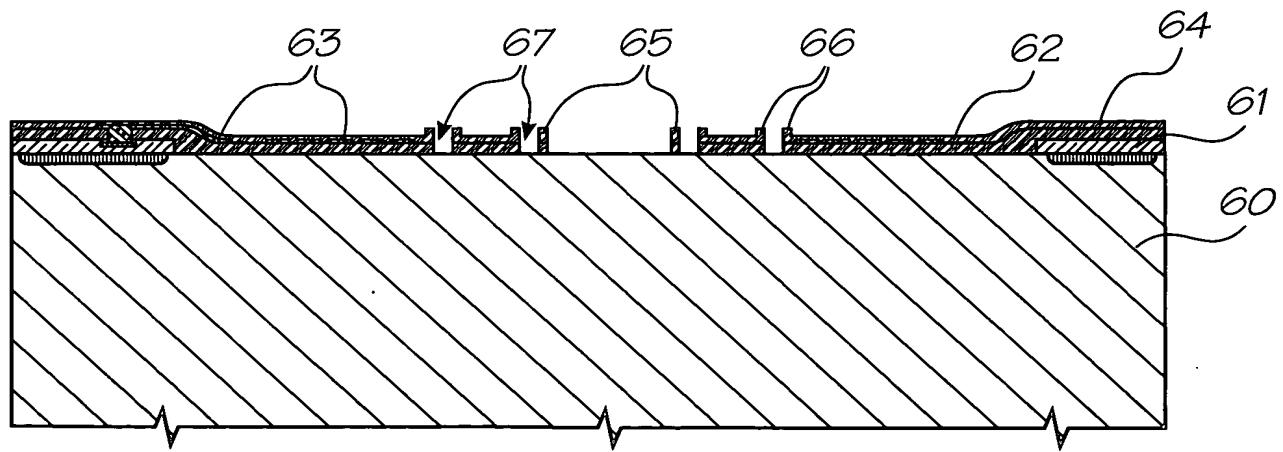


FIG. 20

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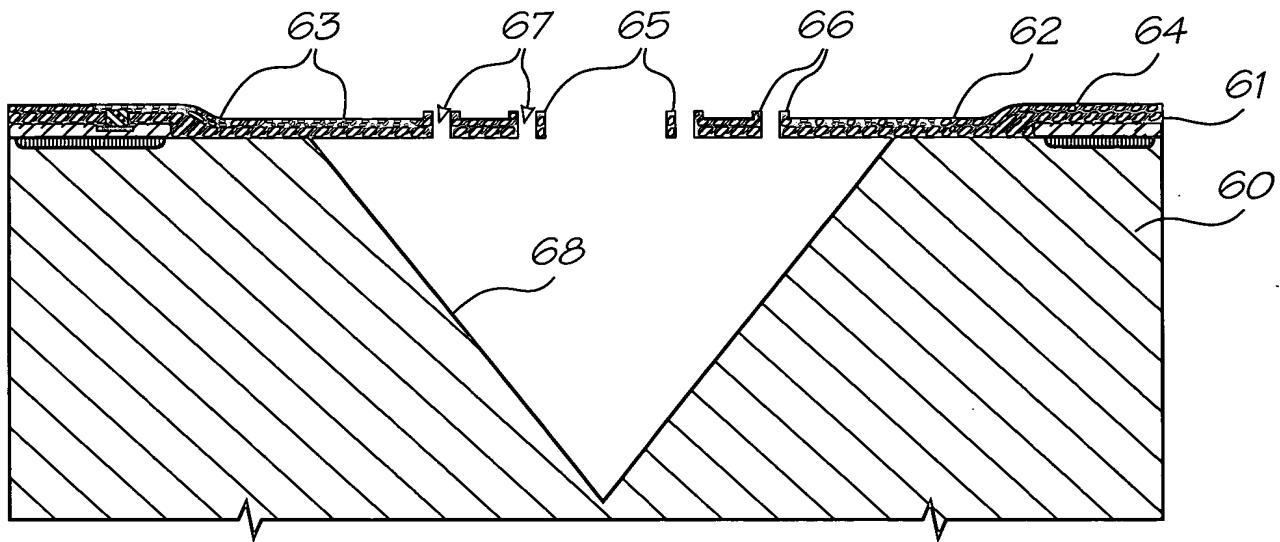


FIG. 21

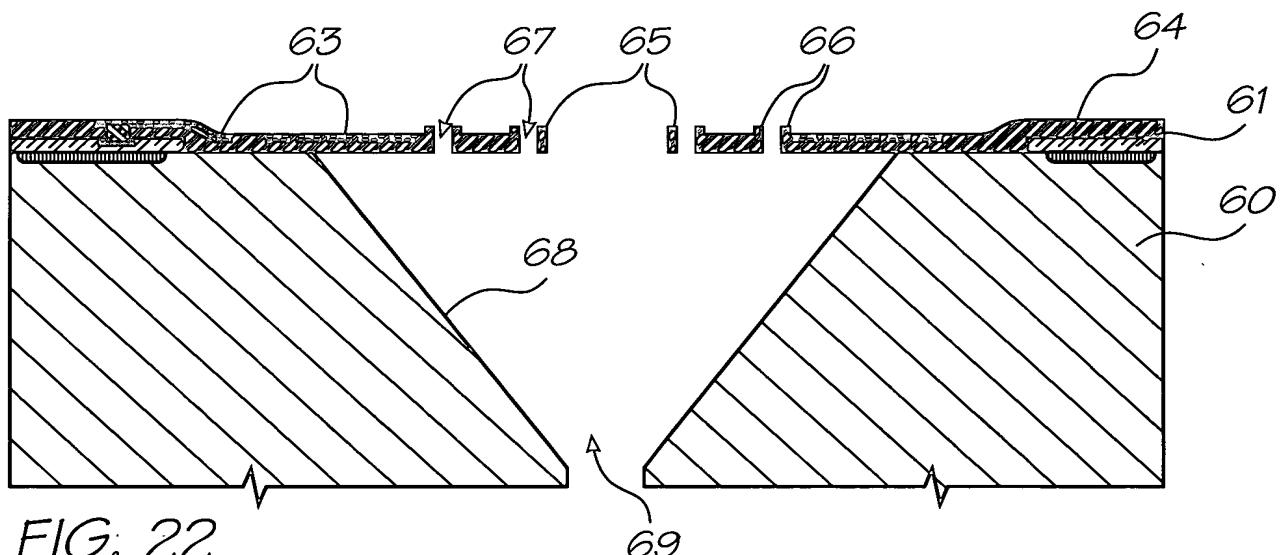


FIG. 22

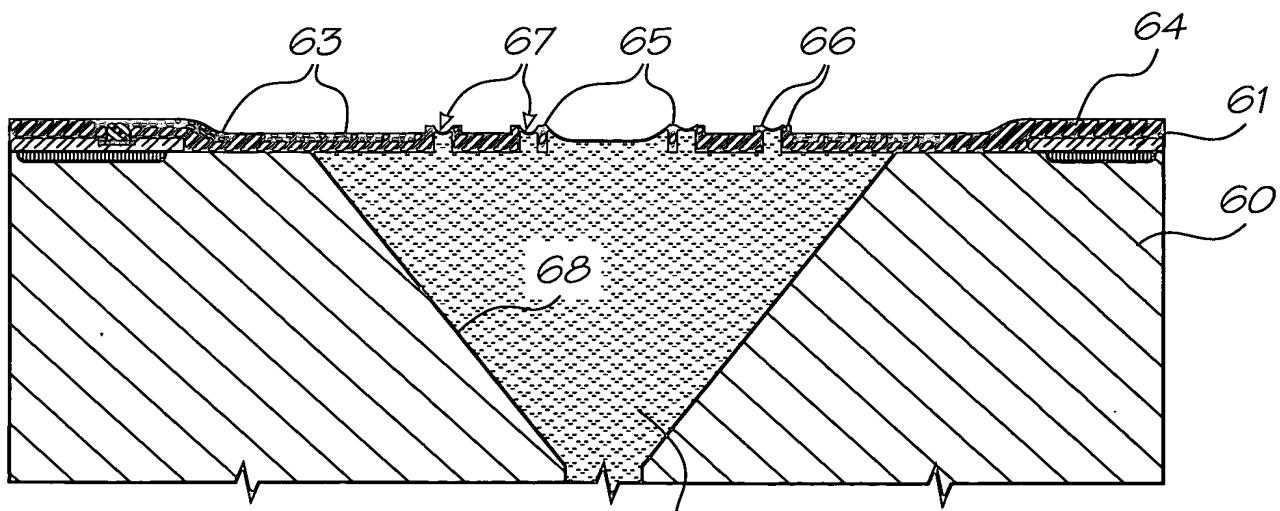


FIG. 23